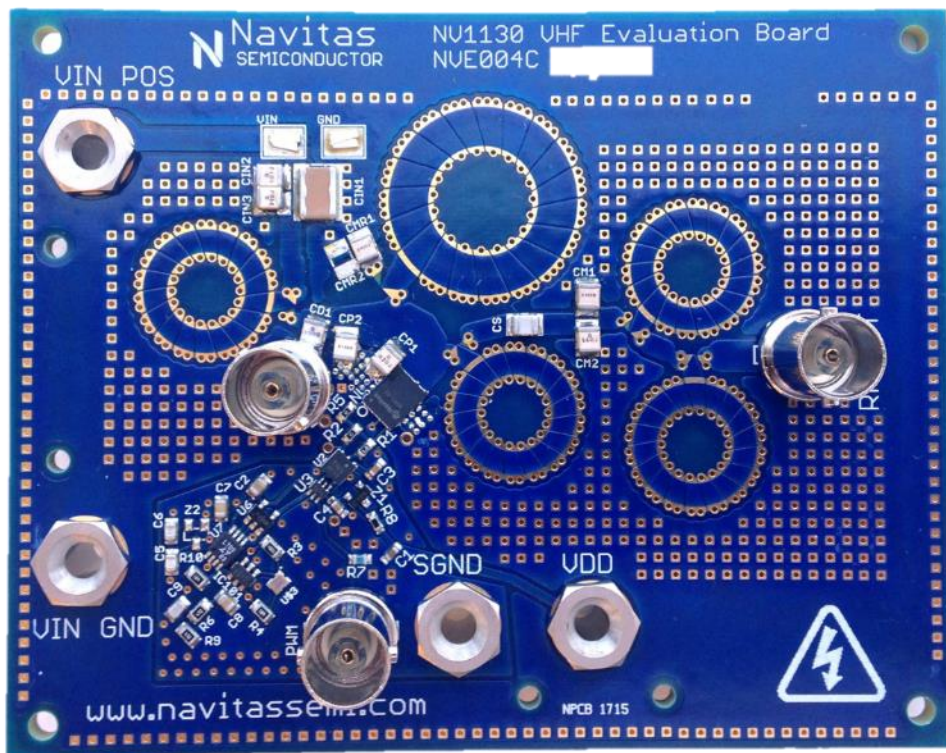
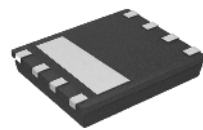


VHF Φ 2 DC-AC Demo Boards

(This user's guide covers both NVE004C-A (27MHz) and NVE004C-B (40MHz) class Φ 2 inverter demo boards with NV1130)

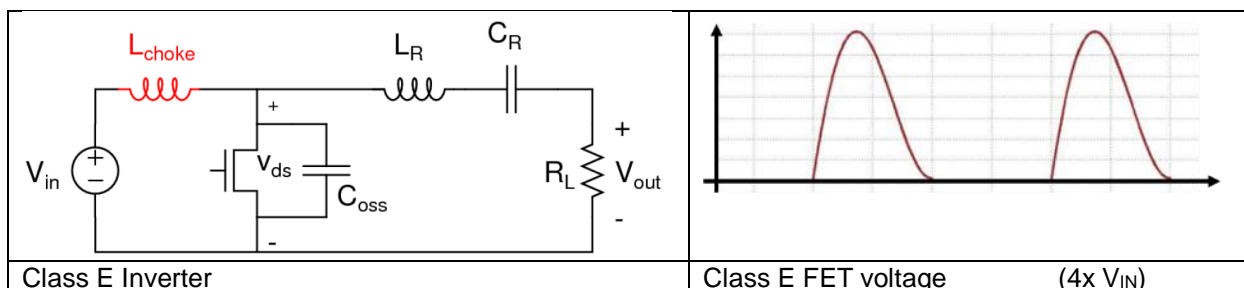
User Guide UG002



Description:

The NV1130 is a 650V 130m Ω eMode GaN Power IC with extremely low gate charge and output capacitance. The Φ 2 demonstration board demonstrates how this performance enables efficient VHF power conversion.

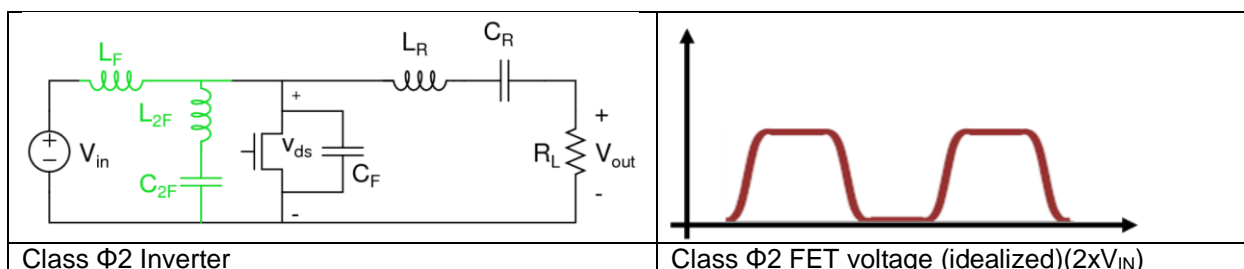
Class E amplifiers (N. Sokal & A. Sokal (1975)) enable very high-frequency switching but FET voltage stress is high ($4x V_{IN}$), meaning high FET losses as $R_{ds(on)}$ increases with voltage.



The class Φ 2 converter (Rivas, Han, Leitermann, Sagneri, Perrault (2008)) removes the 2nd harmonic (the " Φ 2") to limit FET voltage stress to $2x V_{IN}$. As class Φ 2 can now use lower voltage FETs, it is more efficient and can process more power.

For more information, please refer to MIT Open Access Article:

<http://dspace.mit.edu/handle/1721.1/86922>



Additional benefits of the Φ 2 over Class E include:

- Replacing the DC choke with a simple multi-resonant network, eliminating the link between FET capacitance and power (C_F is now chosen as part of the network).
- Elimination of bulk inductance allowing smaller, even 'air core' inductors, with fast transient performance.

Due to industry-leading on-state and switching performance metrics ($R_{DS(ON)} \times Q_g$ and $R_{DS(ON)} \times Q_{oss}$), Navitas GaN Power ICs enable new benchmarks in VHF conversion.

This DC-AC VHF inverter is a building block demonstrator. By Adding an isolation transformer and resonant rectifier, a compact, isolated, DC-DC power supply is possible. Please reference to MIT's papers for additional information.

Start-up Sequence:

1. Connect V_{DD} bias supply, input voltage (V_{IN}), 50Ω load, PWM signal generator and scope probes.
2. Apply V_{DD} (set to 6V, 100mA).
3. Apply PWM input (Max 5% duty cycle, 10kHz, 5V output).
4. Gradually turn on V_{IN} from 0V to $150V_{DC}$.
5. Monitor V_{DS} voltage:
 - a. Multiply scope reading by 10-11x, based on probe input capacitance,
 - b. The correct reading should be about 300-320V peak to peak voltage,
 - c. Due to PWM action, use Normal mode for scope triggering.

Power-down Sequence:

1. Turn off V_{IN} first.

Caution:

1. Make sure 5% or less PWM is applied to avoid load overheating
2. Avoid probing other circuit nodes due to sensitivity to parasitic.

Operation Conditions:

	PARAMETER		Value	UNITS
V_{IN}	Input Voltage		150	V
V_{DD}	Bias Voltage		6	V
PWM	Signal Generator (0-5V, high Z output) duty cycle		5	%
F_{SW}	Switching Frequency	NVE004C-A	27.12	MHz
		NVE004C-A	40	MHz
P_{OUT}	Output Power (max)	NVE004C-A at $150V_{IN}$	150	W
		NVE004C-A at $150V_{IN}$	100	W

Fig. 1:
Board set-up

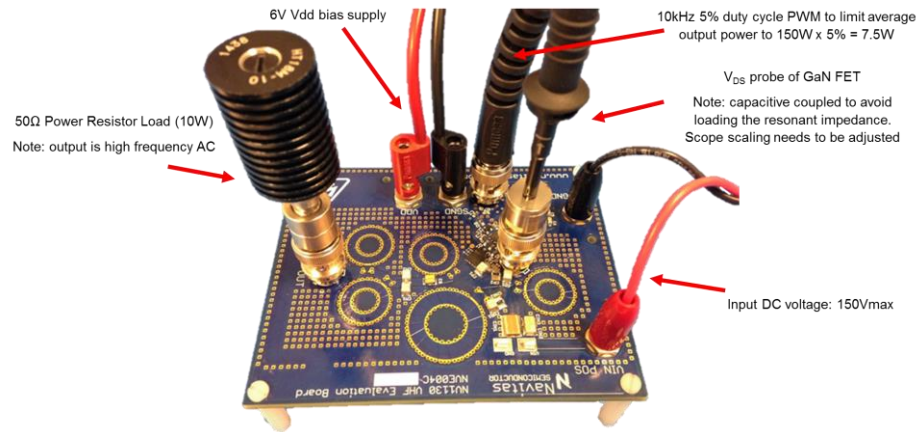


Fig. 2:
V_{DD} power supply and PWM input



Caution: Note peak and average power rating of demo board.
The PWM controls the enable pin of the driver, so the inverter operates in burst mode to limit average output power and protect the 50Ω load.
(100W x 5% = 5W)
(150W x 5% = 7.5W)

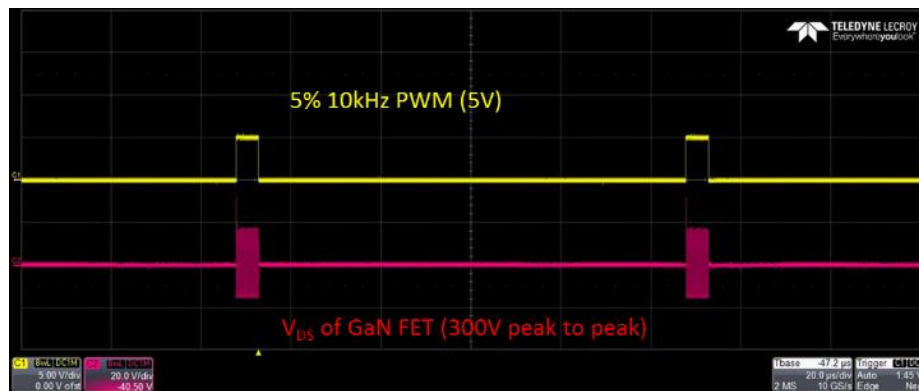


Fig. 3:
High voltage output load connection using 50 Ω RF resistor (10W). Tee adapter enables output voltage measurement and load connection.

<http://www.pasternack.com/10-watts-bnc-male-rf-load-up-to-4-ghz-pe6034-p.aspx>

<http://www.pasternack.com/bnc-male-female-female-tee-adapter-pe9174-p.aspx>

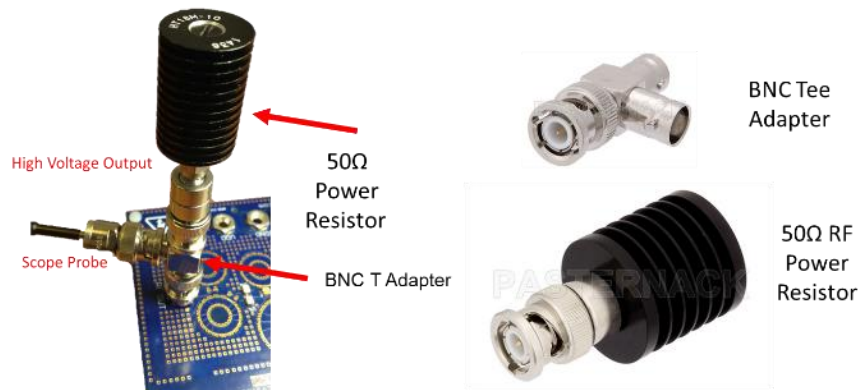


Fig. 4:
High voltage input connection. Max 150V.

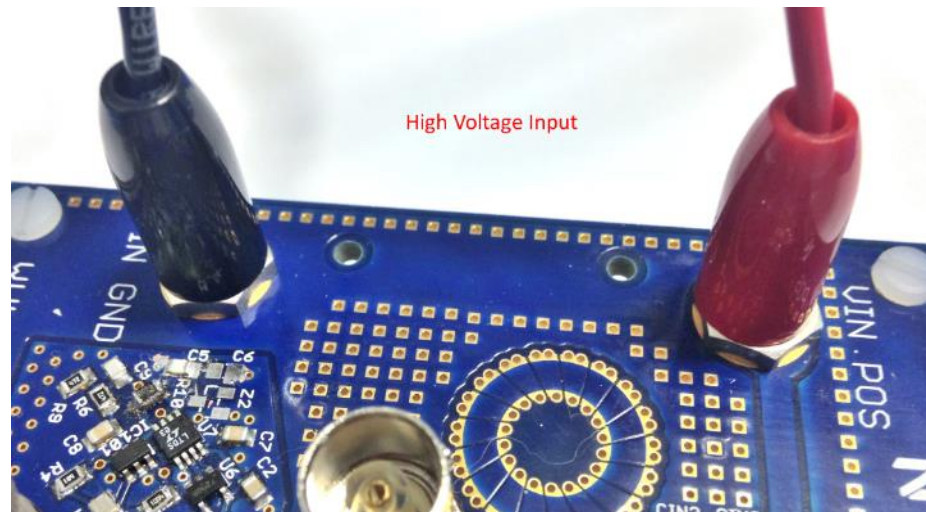


Fig. 5:
PWM signal generator connection. Max 5% 10kHz

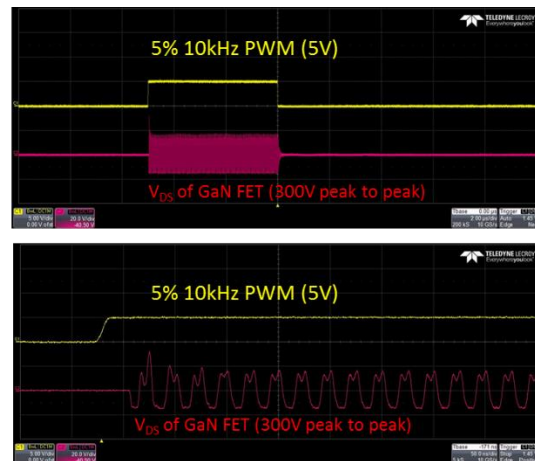
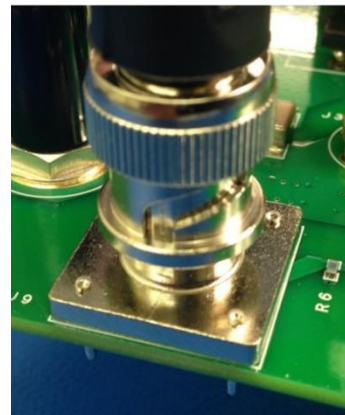


Fig. 6:
Probe location to
measure FET
 V_{DS}

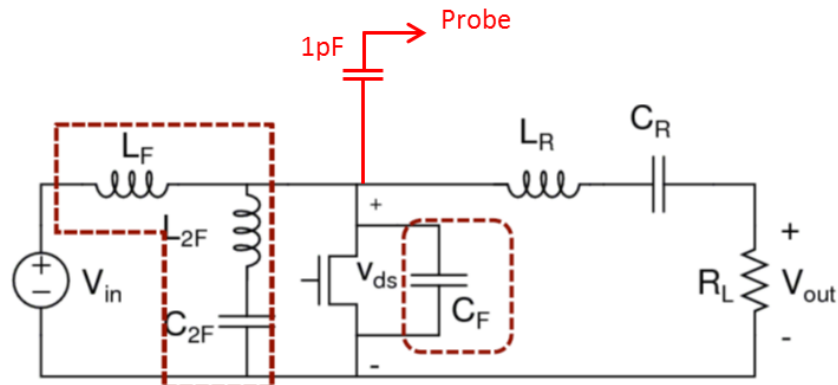


Fig. 7:
Probes:
Probe/BNC
adapter (left) is
preferred
technique
(cleaner
waveform)

<http://www.amazon.com/TEKTRONIX-013022600-PROBE-TIP-ADAPTER/dp/B00DJ S6XLA>

<http://www.caltestelectronics.com/ctitem/35-35mm-probe-accessories/CT3655>

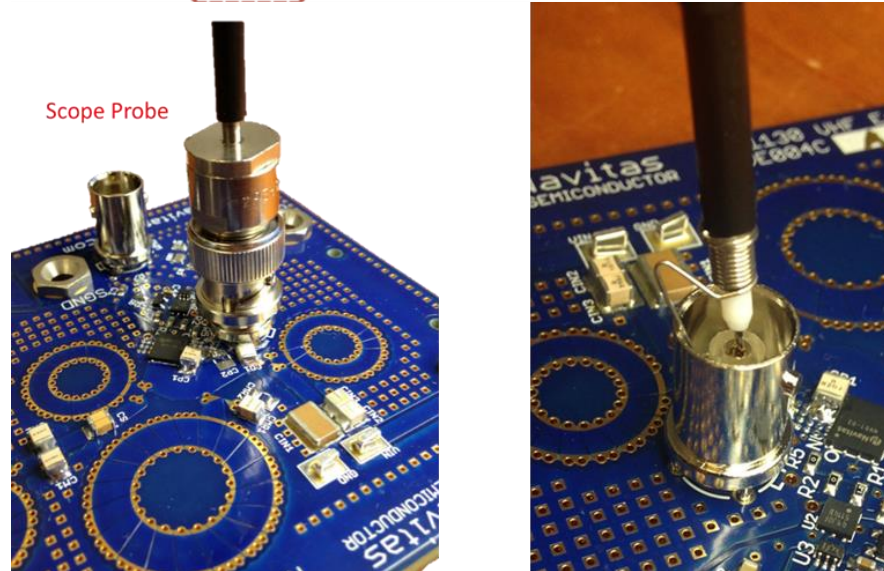
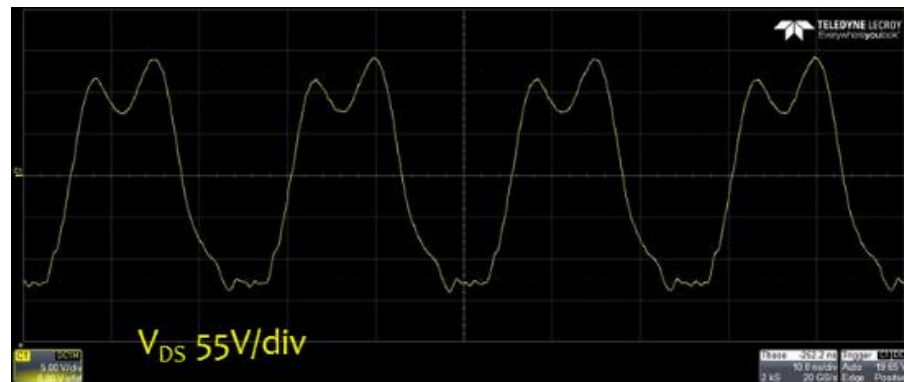


Fig. 8:
Probe
capacitance
interferences
with resonant
capacitor C_F if
used directly to
probe V_{DS} .



Use a 1pF decoupling capacitor to limit the overall probe impact to less than 1pF. The decoupling capacitor and probe capacitor form a capacitor network. The V_{DS} reading needs to be rescaled. At 150V_{IN}, V_{DS} peak to peak voltage should be around 320V. Due to the decoupling capacitor, the DC component of V_{DS} is removed. Use peak to peak voltage to judge V_{DS} magnitude. Note: the 50 Ω load can be directly probed using a T-adaptor. No decoupling capacitor is needed.

Fig. 9: 27.12MHz board FET V_{DS} and Output waveforms

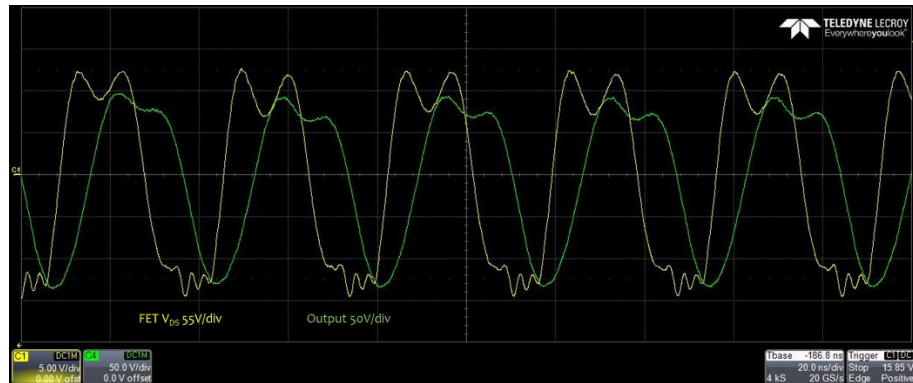


Fig. 10: Start-up.

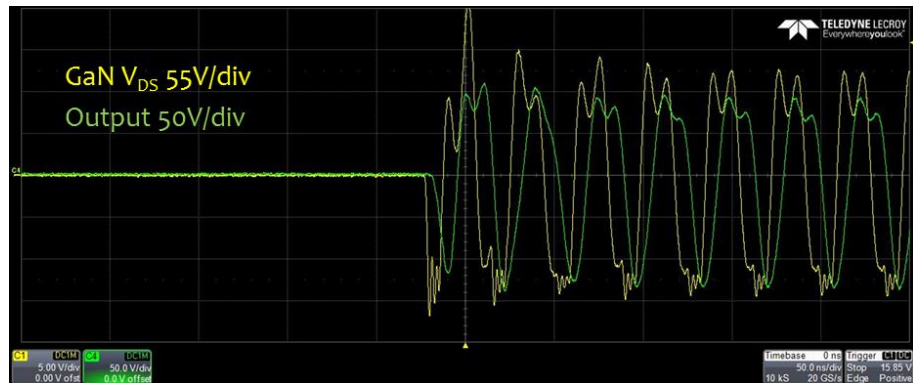


Fig. 11: Pulse-modulated output power

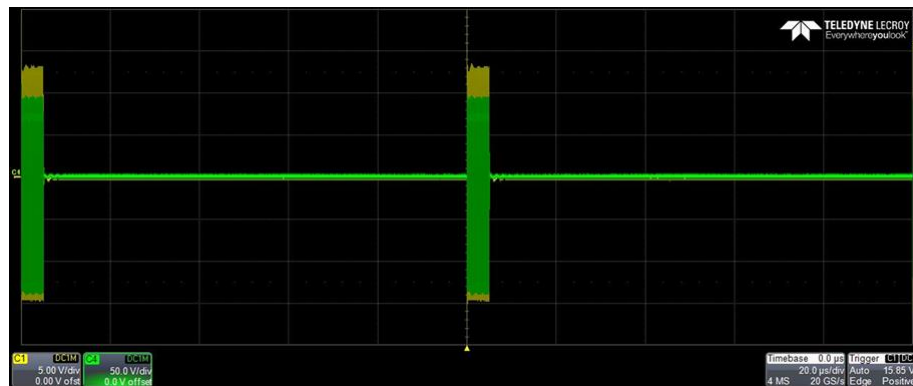


Fig. 12: Steady-state (V_{DS})

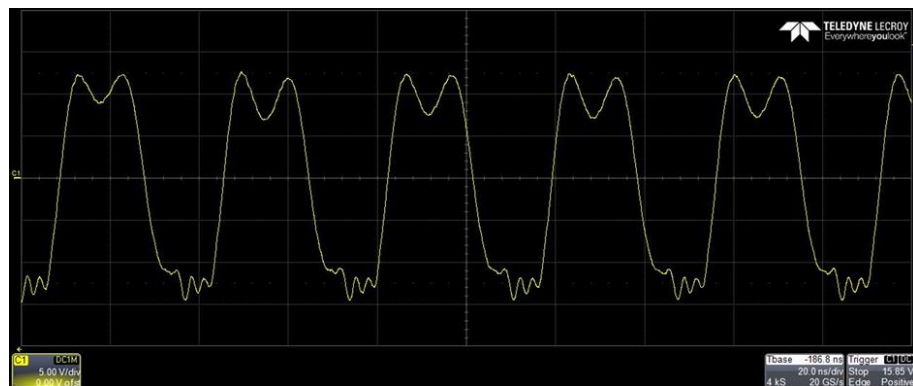


Fig. 13:
40MHz FET V_{DS}
and Output
waveforms

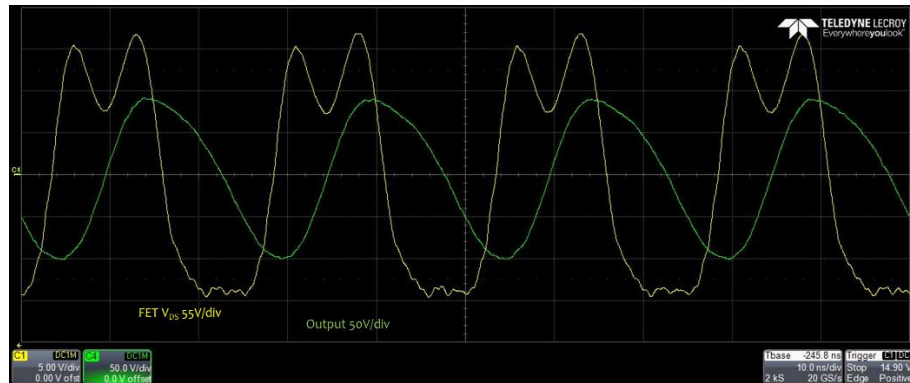


Fig. 14
 V_{DS}

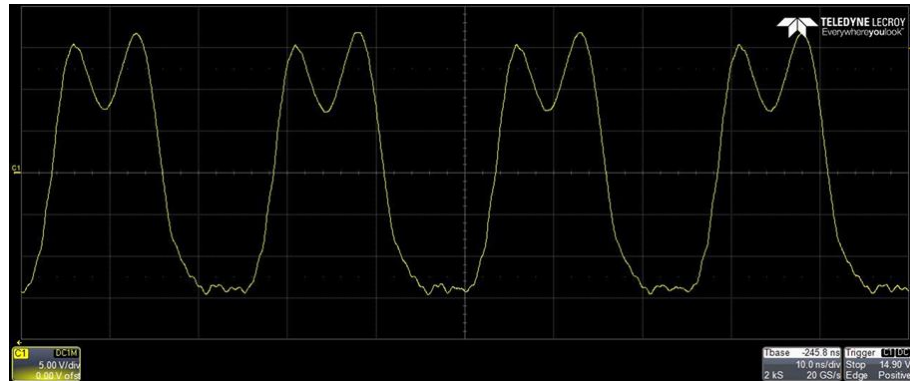


Fig. 15
Output

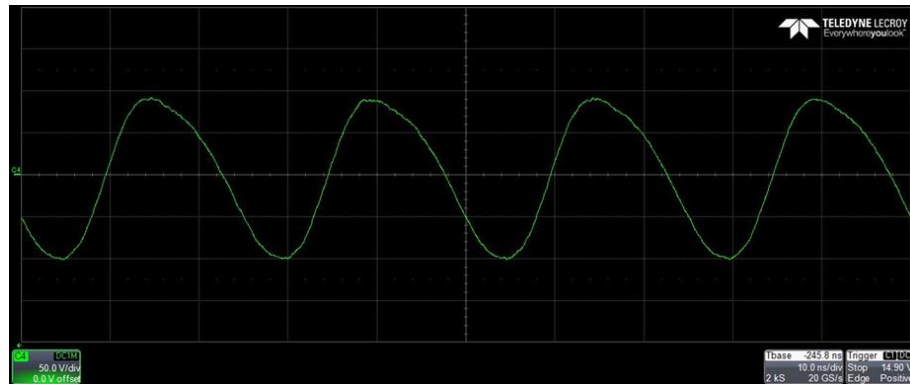


Fig. 16
Start-up
 V_{DS} , Output

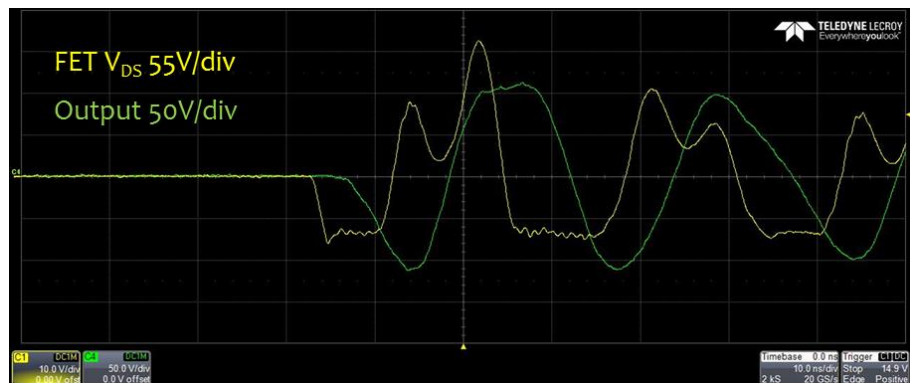


Fig. 17
Pulse-modulated
output power

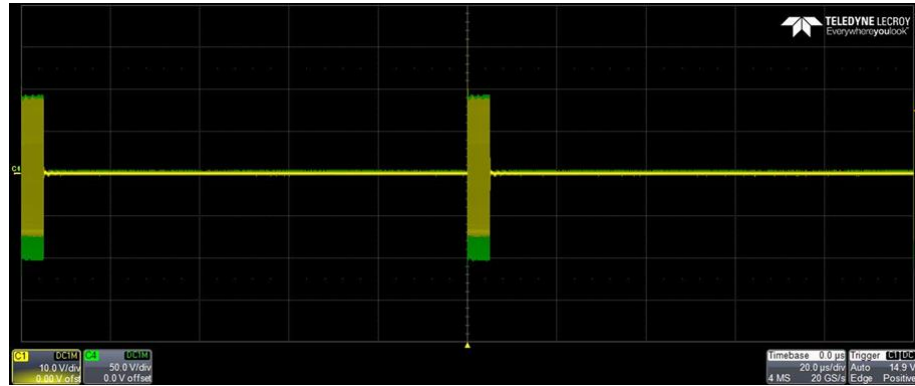
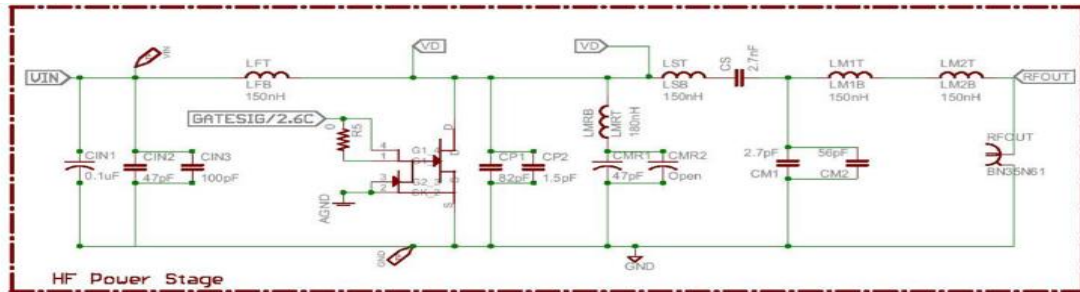


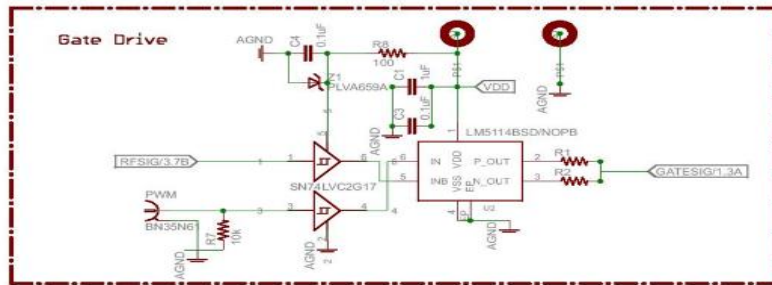
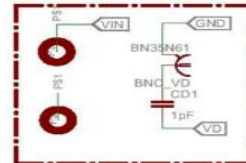
Fig. 18: NVE004C-A 27MHz Schematic



Inputs:
 VIN: 150Vdc, current limit to 1A recommended

Outputs:
 RFOUT: BNC connects to a 50 Ohms load (check power rating)

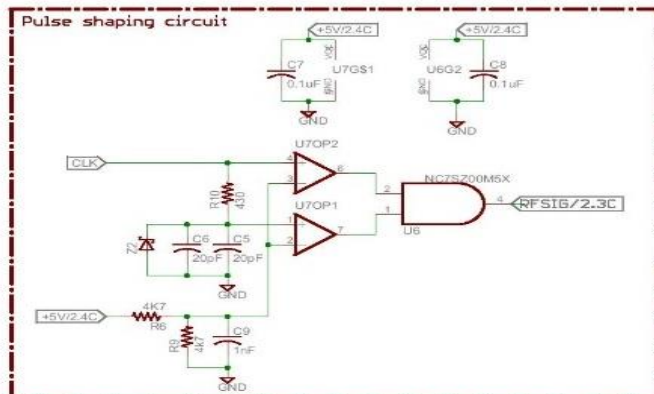
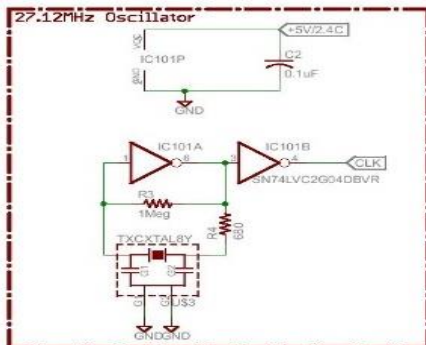
Test points and connectors:
 BNC_UD (grid D6): Drain terminal
 BNC_UD (grid D6): Ac component of Drain voltage.
 Measurement through 1pF (CD1) capacitor divider to prevent loading



Gate Drive:
 RFSIG and low-frequency PWM signals connected to TI-5114 Driver

INPUTS:
 UDD: +6V from an external power supply. Current limit of 600mA recommended

PWM: Digital signal from an external signal generator. TTL levels, freq=1kHz, duty cycle<10%
 Important not to exceed duty cycle without proper heat sinking.

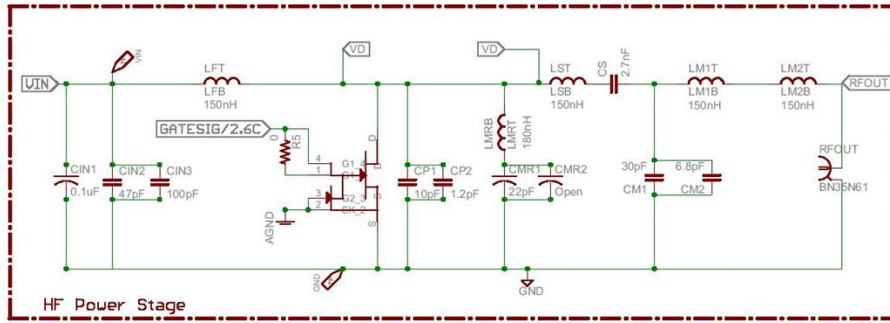


Notes:

RF Oscillator:
 Fixed frequency crystal oscillator circuit

Pulse Shaping Circuit:
 R10, C5, C6 determine the duty cycle of RFSIG

Fig. 19: NVE004C-B 40MHz Schematic

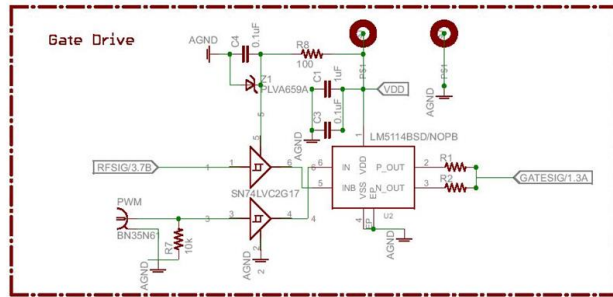
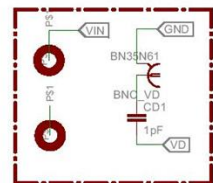


Inputs:
 VIN: 150Vdc, current limit to 1A recommended

Outputs:
 RFOUT: BNC connects to a 50 Ohms load (check power rating)

Test points and connectors:
 BNC_UD (grid D6): Drain terminal

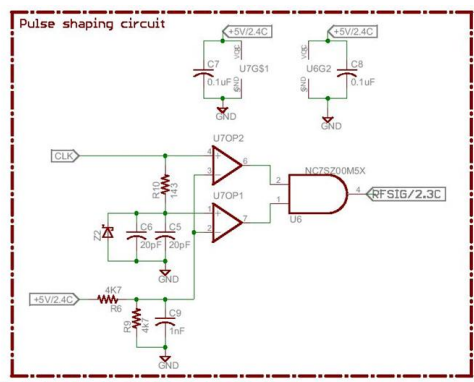
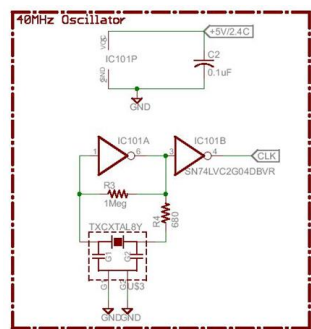
Test points and connectors:
 BNC_UD (grid D6): Ac component of Drain voltage.
 Measurement through 1pF (CD1) capacitor divider to prevent loading



Gate Drive:
 RFSIG and low-frequency PWM signals connected to TI-5114 Driver

INPUTS:
 UDD: +6V from an external power supply. Current limit of 600mA recommended

PWM: Digital signal from an external signal generator. TTL levels, freq=1KH, duty cycle<10%. Important not to exceed duty cycle without proper heat sinking.



Notes:

RF Oscillator:
 Fixed frequency crystal oscillator circuit

Pulse Shaping Circuit:
 R10, C5, C6 determine the duty cycle of RFSIG

Fig. 20: PCB top and bottom layers

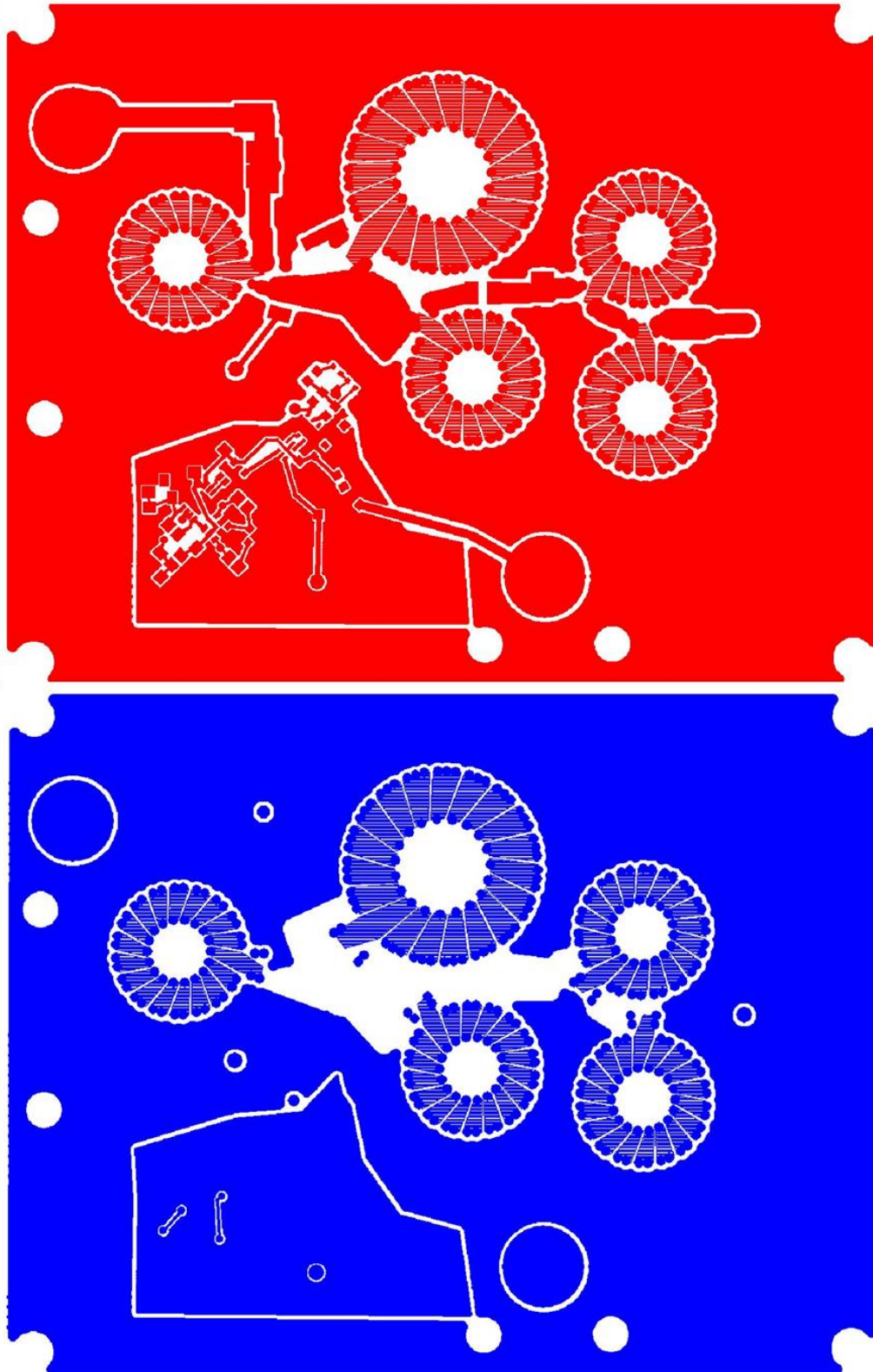


Fig 21: NVE004C-A 27MHz Bill OF Materials

Part	Value	Device	Package	Description	Manufacturer	Mr. Part No.
CIN1	0.1uF, 500V	C1825C104KCRACU	1825	X7R Multi-layer Ceramic Capacitor	Kemet	C1825C104KCRACU
CIN2	47pF	47pF RF Ceramic	C1210	HF Filtering	ATC	
CIN3	100pF	100pF RF Ceramic	C1210	HF Filtering	ATC	
CP1	82pF	20pF RF Ceramic	C1210	Paralell Tuning Capacitor	ATC	
CP2	1.5pF	1.5pF RF Ceramic	C1210	Paralell Tuning Capacitor	ATC	
CMR1	47pF	47pF RF Ceramic	C1210	2nd Harmonic Resonant Capacitor	ATC	
CMR2	None	None	C1210	2nd Harmonic Resonant Capacitor	ATC	
CM1	2.7pF	2.7pF RF Ceramic	C1210	Matching Network Capacitor	ATC	
CM2	56pF	56pF RF Ceramic	C1210	Matching Network Capacitor	ATC	
CD1	1.0pF	1.0pF RF Ceramic	C1210	Drain Measuring Point		
CS	2.7nF	C1210C272KCGACTU	C1210	Inverter Series Blocking Capacitor	Kemet	C1210C272KCGACTU
C1	1uF, 25V	GRM188R61E105KA12D	C0603	Ceramic Capacitor	Murata	GRM188R61E105KA12D
C2	0.1uF, 25V	C0805C104K3RACTU	C0805	Ceramic Capacitor	Kemet	C0805C104K3RACTU
C3	0.1uF, 25V	GRM188R71E104KA01D	C0603	Ceramic Capacitor	Murata	GRM188R71E104KA01D
C4	0.1uF, 25V	GRM188R71E104KA01D	C0603	Ceramic Capacitor	Murata	GRM188R71E104KA01D
C5	20pF, 16V	C0805C200J4GAC7800	C0805	Duty cycle control	Murata	C0805C200J4GAC7800
C6	20pF, 16V	C0805C200J4GAC7800	C0805	Duty cycle control	Murata	C0805C200J4GAC7800
C7	0.1uF, 25V	C0805C104K3RACTU	C0805	Ceramic Capacitor	Kemet	C0805C104K3RACTU
C8	0.1uF, 25V	C0805C104K3RACTU	C0805	Ceramic Capacitor	Kemet	C0805C104K3RACTU
C9	1nF, 25V	08053A102KAT2A	C0805	Ceramic Capacitor	Kemet	08053A102KAT2A
TP1		TPOINTMIN	TPSM5M	SMT/THM Test Point	Keystone Electronics	5015
TP2		TPOINTMIN	TPSM5M	SMT/THM Test Point	Keystone Electronics	5015
SGND				BANANA JACK		
VDD				BANANA JACK		
VIN						
GND				BANANA JACK		
VOUT						
GND				BANANA JACK		
Q1		NV1130	QFN	650V Mosfet	Navitas Semiconductor	
R1	1, 1/10w, 5%	ERJ-3RQF1R0V	R0603	Resistor	Panasonic	ERJ-3RQF1R0V
R2	0, 1/10w, 5%	ERJ-3GEY0R00V	R0603	Resistor	Panasonic	ERJ-3GEY0R00V
R3	1M, 1/8w, 5%	ERJ-6ENF1004V	R0805	Resistor	Panasonic	ERJ-6ENF1004V
R4	680, 1/8w, 5%	ERJ-6GEYJ681V	R0805	Resistor	Panasonic	ERJ-6GEYJ681V
R5	0, 1/10w, 5%	ERJ-3GEY0R00V	R0603	Resistor	Panasonic	ERJ-3GEY0R00V
R6	4k7, 1/8w, 5%	ERJ-6GEYJ472V	R0805	Resistor	Panasonic	ERJ-6GEYJ472V
R7	10k, 1/10w, 5%	ERJ-3GEYJ103V	R0603	Resistor	Panasonic	ERJ-3GEYJ103V
R8	100, 1/10w, 5%	ERJ-3GEYJ101V	R0603	Resistor	Panasonic	ERJ-3GEYJ101V
R9	4k7, 1/8w, 5%	ERJ-6GEYJ472V	R0805	Resistor	Panasonic	ERJ-6GEYJ472V
R10	430, 1/8w, 5%	ERJ-6GEYJ431V	R0805	Resistor	Panasonic	ERJ-6GEYJ431V
RFOUT	Female BNC	5-1634503-1	BNC	RF for 50 OHM Load	TE Connectivity AMP Connectors	5-1634503-1
PWM	Female BNC	5-1634503-1	BNC	PWM Input	TE Connectivity AMP Connectors	5-1634503-1
Drain	Female BNC	5-1634503-1	BNC	Drain Measuring Point	TE Connectivity AMP Connectors	5-1634503-1
Z1		PLVA650A,215	SOT23	5.0 Zener Diode 250mW	NXP Semiconductors	PLVA650A,215
Z2		None				
U2		LM5114BSD/NOPB	6-WDFN	MOSFET Driver	Texas Instruments	LM5114BSD/NOPB
U3		SN74LVC2G17	SC70	Dual Buffer	Texas Instruments	SN74LVC2G17
IC101		SN74LVC2G04DBVR	SOT23	Dual Inverter	Texas Instruments	SN74LVC2G04DBVR
U\$3		8Y-27.120MEEQ-T		Clock	TXC	8Y-27.120MEEQ-T
U6		NC7SZ00M5X	SOT23-5	NAND	Fairchild	NC7SZ00M5X
U7		LT1720CMS8#PBF	8-MSOP	Rail-Rail Comparitor	Linear	LT1720CMS8#PBF

Fig 21: NVE004C-A 27MHz Bill OF Materials

Part	Value	Device	Package	Description	Manufacturer	Mr. Part No.
CIN1	0.1uF, 500V	C1825C104KCRACU	1825	X7R Multi-layer Ceramic Capacitor	Kemet	C1825C104KCRACU
CIN2	47pF	47pF RF Ceramic	C1210	HF Filtering	ATC	
CIN3	100pF	100pF RF Ceramic	C1210	HF Filtering	ATC	
CP1	10pF	10pF RF Ceramic	C1210	Paralell Tuning Capacitor	ATC	
CP2	1.2pF	1.2pF RF Ceramic	C1210	Paralell Tuning Capacitor	ATC	
CMR1	22pF	22pF RF Ceramic	C1210	2nd Harmonic Resonant Capacitor	ATC	
CMR2	Open	Open	C1210	2nd Harmonic Resonant Capacitor	ATC	
CM1	30pF	30pF RF Ceramic	C1210	Matching Network Capacitor	ATC	
CM2	6.8pF	6.8pF RF Ceramic	C1210	Matching Network Capacitor	ATC	
CD1	1.0pF	1.0pF RF Ceramic	C1210	Drain Measuring Point		
CS	2.7nF	C1210C272KCGACT U	C1210	Inverter Series Blocking Capacitor	Kemet	C1210C272KCGACTU
C1	1uF, 25V	GRM188R61E105KA1 2D	C0603	Ceramic Capacitor	Murata	GRM188R61E105KA12D
C2	0.1uF, 25V	C0805C104K3RACTU	C0805	Ceramic Capacitor	Kemet	C0805C104K3RACTU
C3	0.1uF, 25V	GRM188R71E104KA0 1D	C0603	Ceramic Capacitor	Murata	GRM188R71E104KA01D
C4	0.1uF, 25V	GRM188R71E104KA0 1D	C0603	Ceramic Capacitor	Murata	GRM188R71E104KA01D
C5	20pF, 16V	C0805C200J4GAC78 00	C0805	Duty cycle control	Murata	C0805C200J4GAC7800
C6	20pF, 16V	C0805C200J4GAC78 00	C0805	Duty cycle control	Murata	C0805C200J4GAC7800
C7	0.1uF, 25V	C0805C104K3RACTU	C0805	Ceramic Capacitor	Kemet	C0805C104K3RACTU
C8	0.1uF, 25V	C0805C104K3RACTU	C0805	Ceramic Capacitor	Kemet	C0805C104K3RACTU
C9	1nF, 25V	08053A102KAT2A	C0805	Ceramic Capacitor	Kemet	08053A102KAT2A
TP1		TPOINTMIN	TPSM5DM	SMT/THM Test Point	Keystone Electronics	5015
TP2		TPOINTMIN	TPSM5DM	SMT/THM Test Point	Keystone Electronics	5015
SGND				BANANA JACK		
VDD				BANANA JACK		
VIN GND				BANANA JACK		
VOUT GND				BANANA JACK		
Q1		NV1130	QFN	650V Mosfet	Navitas Semiconductor	
R1	1, 1/10w, 5%	ERJ-3RQF1R0V	R0603	Resistor	Panasonic	ERJ-3RQF1R0V
R2	0, 1/10w, 5%	ERJ-3GEY0R00V	R0603	Resistor	Panasonic	ERJ-3GEY0R00V
R3	1M, 1/8w, 5%	ERJ-6ENF1004V	R0805	Resistor	Panasonic	ERJ-6ENF1004V
R4	680, 1/8w, 5%	ERJ-6GEYJ681V	R0805	Resistor	Panasonic	ERJ-6GEYJ681V
R5	0, 1/10w, 5%	ERJ-3GEY0R00V	R0603	Resistor	Panasonic	ERJ-3GEY0R00V
R6	4k7, 1/8w, 5%	ERJ-6GEYJ472V	R0805	Resistor	Panasonic	ERJ-6GEYJ472V
R7	10k, 1/10w, 5%	ERJ-3GEYJ103V	R0603	Resistor	Panasonic	ERJ-3GEYJ103V
R8	100, 1/10w, 5%	ERJ-3GEYJ101V	R0603	Resistor	Panasonic	ERJ-3GEYJ101V
R9	4k7, 1/8w, 5%	ERJ-6GEYJ472V	R0805	Resistor	Panasonic	ERJ-6GEYJ472V
R10	143, 1/8w, 5%	ERJ-6ENF1430V	R0805	Duty cycle control	Panasonic	ERJ-6ENF1430V
RFOUT	Female BNC	5-1634503-1	BNC	RF for 50 OHM Load	TE Connectivity AMP Connectors	5-1634503-1
PWM	Female BNC	5-1634503-1	BNC	PWM Input	TE Connectivity AMP Connectors	5-1634503-1
Drain	Female BNC	5-1634503-1	BNC	Drain Measuring Point	TE Connectivity AMP Connectors	5-1634503-1
Z1		PLVA650A,215	SOT23	5.0 Zener Diode 250mW	NXP Semiconductors	PLVA650A,215
Z2		TBD				
U2		LM5114BSD/NOPB	6-WDFN	MOSFET Driver	Texas Instruments	LM5114BSD/NOPB
U3		SN74LVC2G17	SC70	Dual Buffer	Texas Instruments	SN74LVC2G17
IC101		SN74LVC2G04DBVR	SOT23	Dual Inverter	Texas Instruments	SN74LVC2G04DBVR
US3		8Y-40.000MAAV-T		Clock	TXC	8Y-40.000MAAV-T
U6		NC7SZ00M5X	SOT23-5	NAND	Fairchild	NC7SZ00M5X
U7		LT1720CMS8#PBF	8-MSOP	Rail-Rail Comparitor	Linear	LT1720CMS8#PBF